Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20040213310"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:02
L2	2	1 & (low (al resistanc$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:02
L3	2	1 & (low with (al resistanc$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:03
L4	2	3 & (active with (layer region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:05
L5	2	1 & (active with (layer region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:05
L6	2	1 & (active near5 (layer region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:13
L7	1594161	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:13
L8	145963	semiconductor with laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:19

L9	19750	8 & ((mirror reflect$3) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:20
L10	7347	9 & (active near5 (region layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:20
L11	140735	semiconductor near12 laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:19
L12	140735	11 & (surfac$3 near5 emitt$3 sear5 semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:20
L13	19029	12 & ((mirror reflect$3) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:20
L14	7144	13 & (active near5 (region layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:21
L15	1888	14 & ((confin$3 confinement) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:22
L16	1847	15 & substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:22

L17	165	16 & ((low with (al resistance)) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:58
L18	143	17 & rat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:25
L19	0	17 & (compost$3 with rat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:25
L20	62	17 & (composit$3 with rat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:26
L21	53	17 & (composit$3 near5 rat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:28
L22	44	21 & ((low near5 resistance) with (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:29
L23	43	21 & ((low near5 resistance) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:30
L24	1	1 & diode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:31

L25	0	23 & vcsal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:32
L26	7	23 & vcsel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:57
L27	6	"6765232"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 13:57
L28	3	27 & ((low with (al resistance)) near5 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:02
L29	3	28 & (intermedia$3 near3 (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:09
L30	3	29 & method & etch$3 & form$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 14:19
S1	21	(hiromi near1 otoma).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 15:55
S2	20	S1 & semiconductor & laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:55

S3	19	S2 & substrat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:56
S4	13	S3 & (reflect$3 near5 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:01
S5	13	S4 & layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:01
S6	13	S5 & active	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:02
S7	12	S6 & resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:02
S8	12	S7 & first & second	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:04
S9	7	S8 & (current with confin$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:06
S10	12	S8 & (current with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:29

S11	2	"20040213310"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:29
S12	2	S11 & (current with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:29
S13	162036	semiconductor same laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:55
S14	12889	S13 & (reflect$3 with film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:56
S15	5379	S13 & (reflect$3 with film with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 16:56
S16	4628	S15 & substrat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:05
S17	1278	S16 & (resistance with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:06
S18	73	S17 & (current with confin$3 with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:07

S19	72	S18 & (layer with (active region))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:16
S20	13630	S19 & ow wv	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:20
S21	162036	semiconductor same laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:44
S22	16353	surface same emitt$3 same semiconduct$3 same laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:46
S23	6539	S22 & (reflect$3 same (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:46
S24	3873	S23 & (active same (region layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:47
S25	2434	current with confin$3 with layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:18
S26	339	S24 & S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 17:48

S27	97	S26 & (low same resistance same layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:21
S28	97	S27 & substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:22
S29	16	S28 & (space same layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:22
S30	8	S29 & (low with resistance with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:36
S31	9	"6201825"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:16
S32	2169	current near5 (confin$3 confinement) near5 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:19
S33	577	S22 & S32	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:19
S34	442	S24 & S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:19

S35	112	S34 & (low same resistance same layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:21
S36	112	S35 & substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:22
S37	14	S36 & (space near5 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:37
S38	2	"20040213310"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:33
S39	2	S38 & (low with resistance with layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:33
S40	12	S29 & (low near5 ((al (resistance near5 layer))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:37
S41	114	S34 & (low near5 ((al (resistance near5 layer))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/14 18:37
S42	13	S41 & (space near5 layer) & substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/15 12:58